

IN THE CLAIMS:

Please amend the claims as follows:

Claims 1-8 (Canceled)

9. (currently amended) A heat treating method ~~for comprising the steps of~~
~~distributing defects in a silicon single crystal wafer, said wafer comprising a surface region of~~
~~several tens of μm deep and an adjacent central region, said wafer having been prepared from a~~
~~perfect crystal free from grown-in defects and produced by a Czochralski method, said defects~~
~~being uniformly distributed in a region consisting essentially of the central region a silicon single~~
~~crystal wafer related to a perfect crystal produced by a Czochralski method, comprising~~by a first
step of maintaining a first heat treatment temperature for an initial entry of the silicon single crystal
wafer up to 500°C, and a second step of maintaining a temperature ramping rate in a temperature
range from the first heat treatment temperature to a second heat treatment temperature of 700°C-
900°C, said ramping rate being 1°C/min or less, ~~said first step being performed first after a wafer~~
~~slicing process.~~

10. (currently amended) A heat treating method ~~for comprising the steps of~~
~~distributing defects in a silicon single crystal wafer, said wafer comprising a surface region of~~
~~several tens of μm deep and an adjacent central region, said wafer having been prepared from a~~
~~perfect crystal free from grown-in defects and produced by a Czochralski method, said defects~~
~~being uniformly distributed in a region consisting essentially of the central region a silicon single~~
~~crystal wafer related to a perfect crystal produced by a Czochralski method, comprising~~by a first
step of maintaining a first heat treatment temperature for an initial entry of the silicon single crystal
wafer up to 500°C, and a second step of maintaining a temperature ramping rate in a temperature
range from the first heat treatment temperature to a second heat treatment temperature of 700°C-
900°C, said ramping rate being 1C/min or less, so as to make uniform the distribution of an oxide
precipitate density of the silicon single crystal wafer in the wafer, said first step being performed
first after a wafer slicing process.

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